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OVAL DEFECTS IN CRYSTALS GROWN BY MBE TECHNIQUE: STUDY AND METHODS OF ELIMINATION

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ABSTRACT

The paper is devoted to a group of macroscopic defects which may be found in epitaxial A^3B^5 materials grown by MBE technique. Morphology, geometry and optical properties of defects were studied by means of several experimental methods. The experimental data have been compared with the information taken from literature concerning sources of the defects and causes of their appearance.